

L Number	Hits	Search Text	DB	Time stamp
1	681	349/20-22.ccls. 349/161.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 10:45
2	1	(349/20-22.ccls. 349/161.ccls.) and (dummy adj cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 10:45
3	1008	heat\$3 near10 ((embed\$4 buried burying bury inside) near6 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 10:45
4	20	(heat\$3 near10 ((embed\$4 buried burying bury inside) near6 cell)) and 349/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 11:10
5	2	"20020089638"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 11:20
6	90	conductive near3 spacer near6 seal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 11:21
7	146	conduct\$3 near3 spacer near6 seal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 11:21
8	67	(conduct\$3 near3 spacer near6 seal\$3) and (heat\$3 (temperature near3 control\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 11:22
9	27	((conduct\$3 near3 spacer near6 seal\$3) and (heat\$3 (temperature near3 control\$4))) and (display LCD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 12:13
10	4	DSTN and heater	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 12:13
11	4	DSTN and (heating near3 element)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 12:13
12	4	DSTN and heater	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 12:13

13	7	(DSTN and (heating near3 element)) (DSTN and heater)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 12:13
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L Number	Hits	Search Text	DB	Time stamp
1	1	2000JP-0013220.ap,prai.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 14:15
2	934	349/\$.ccls. and ((heating near3 element) heater)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 14:20
3	364	(349/\$.ccls. and ((heating near3 element) heater)) and (plural multiple multi two three several) adj2 (layer panel substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 14:20
4	1136	349/\$.ccls. and ((heating near3 (device element structure)) heater)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 14:21
5	690	conduct\$3 near3 spacer same seal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 14:22
6	7	(349/\$.ccls. and ((heating near3 (device element structure)) heater)) and (conduct\$3 near3 spacer same seal\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 14:43